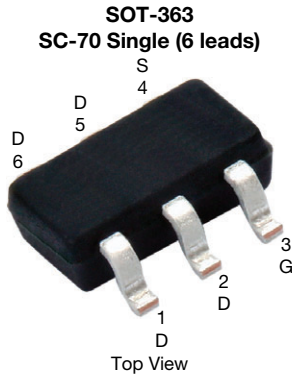


Automotive N-Channel 60 V (D-S) 175 °C MOSFET



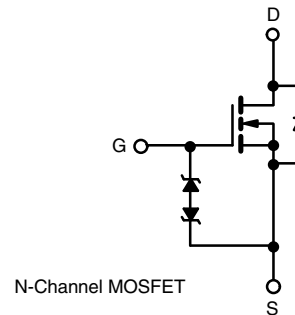
Marking code: 8B

PRODUCT SUMMARY	
V_{DS} (V)	60
$R_{DS(on)}$ (Ω) at $V_{GS} = 1.5$ V	1.41
I_D (A)	0.44
Configuration	Single
Package	SC-70

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g tested
- Typical ESD protection: 800 V
- Material categorization:
for definitions of compliance please see www.vishay.com/doc?99912

 AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE


ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V_{DS}	60	V	
Gate-source voltage	V_{GS}	± 8		
Continuous drain current ^a	I_D	$T_C = 25$ °C	0.44	A
		$T_C = 125$ °C	0.25	
Continuous source current (diode conduction) ^a	I_S	0.54		
Pulsed drain current ^b	I_{DM}	1.7		
Maximum power dissipation ^b	P_D	$T_C = 25$ °C	0.43	W
		$T_C = 125$ °C	0.14	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-ambient	R_{thJA}	460	°C/W	
Junction-to-foot (drain)	R_{thJF}	350		

Notes

- Package limited
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)

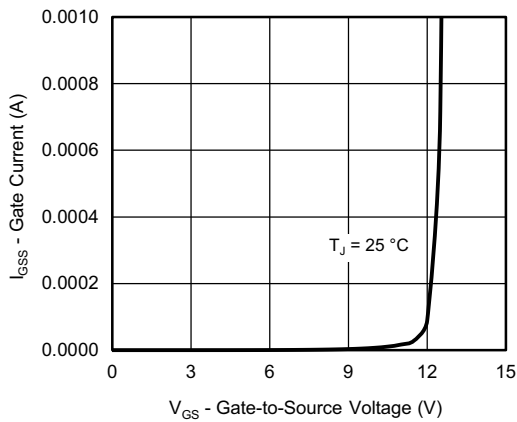
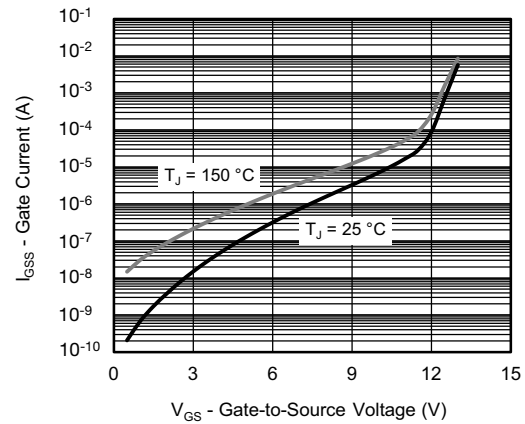
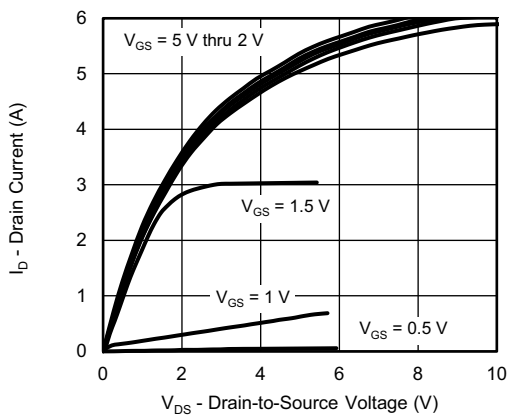
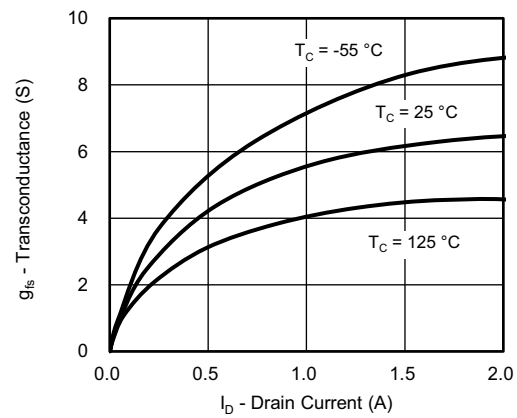
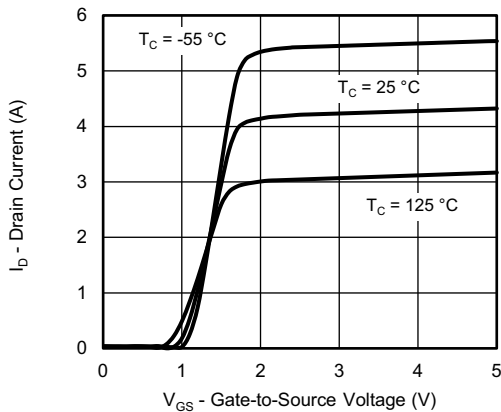
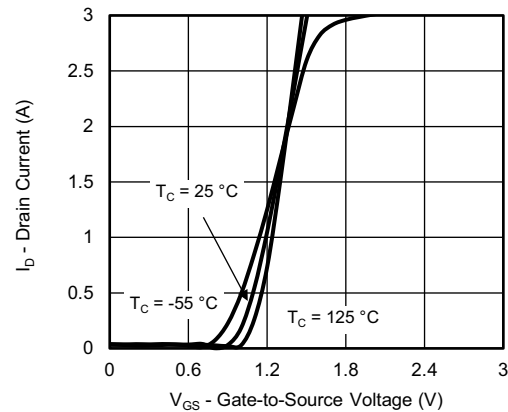


SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA		60	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		0.45	0.6	1	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 3 V		-	-	± 100	nA
		V _{DS} = 0 V, V _{GS} = ± 8 V		-	-	100	
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	150	
On-state drain current ^a	I _{D(on)}	V _{GS} = 1.5 V	V _{DS} ≥ 5 V	0.5	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 1.5 V	I _D = 2 A	-	0.8	1.41	Ω
		V _{GS} = 1.5 V	I _D = 1.2 A, T _J = 125 °C	-	-	2.4	
		V _{GS} = 1.5 V	I _D = 1.2 A, T _J = 175 °C	-	-	3.1	
Forward transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 1 A		-	5.5	-	S
Dynamic ^b							
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	110	140	pF
Output capacitance	C _{oss}			-	19	24	
Reverse transfer capacitance	C _{rss}			-	12	15	
Total gate charge ^c	Q _g	V _{GS} = 4.5 V	V _{DS} = 30 V, I _D = 2.8 A	-	2.7	4.1	nC
Gate-source charge ^c	Q _{gs}			-	0.25	-	
Gate-drain charge ^c	Q _{gd}			-	0.35	-	
Gate resistance	R _g	f = 1 MHz		5.8	9	15.5	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 30 Ω I _D ≅ 1 A, V _{GEN} = 4.5 V, R _g = 1 Ω		-	12	18	ns
Rise time ^c	t _r			-	21	32	
Turn-off delay time ^c	t _{d(off)}			-	8	12	
Fall time ^c	t _f			-	7	11	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I _{SM}			-	-	1.6	A
Forward voltage	V _{SD}	I _F = 0.8 A, V _{GS} = 0		-	0.8	1.2	V

Notes

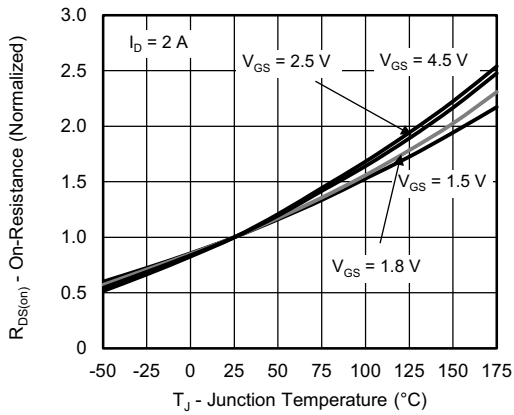
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

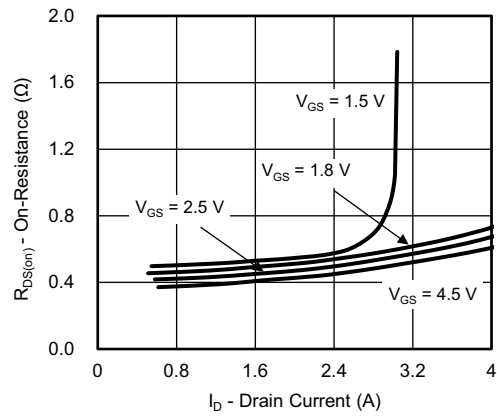
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Gate Current vs. Gate-Source Voltage

Gate Current vs. Gate-Source Voltage

Output Characteristics

Transconductance

Transfer Characteristics

Transfer Characteristics



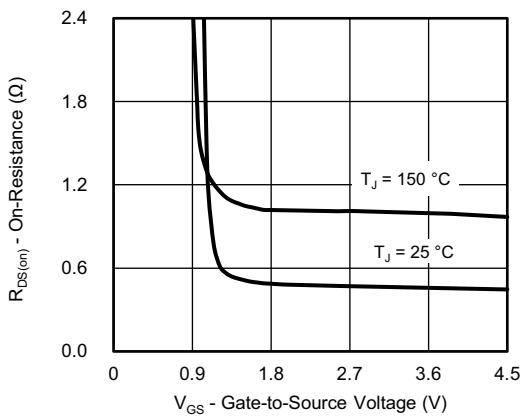
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



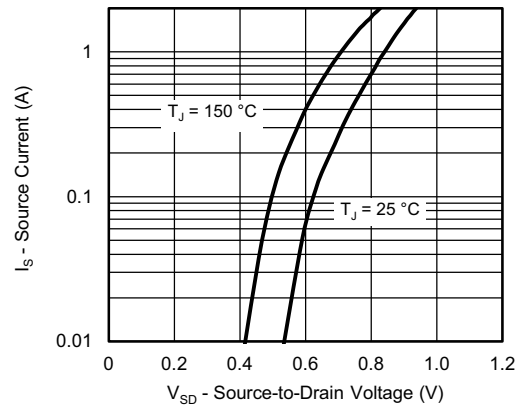
On-Resistance vs. Junction Temperature



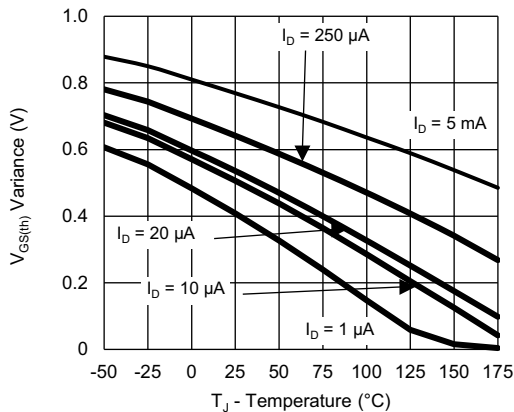
On-Resistance vs. Drain Current



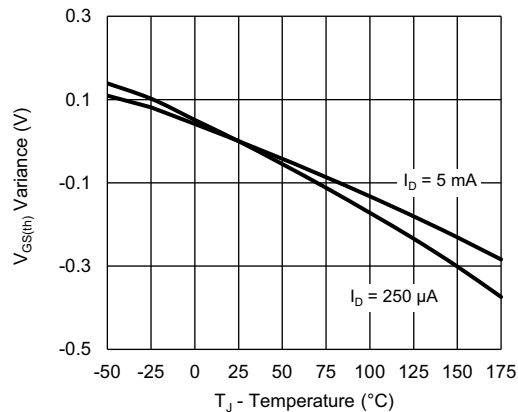
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



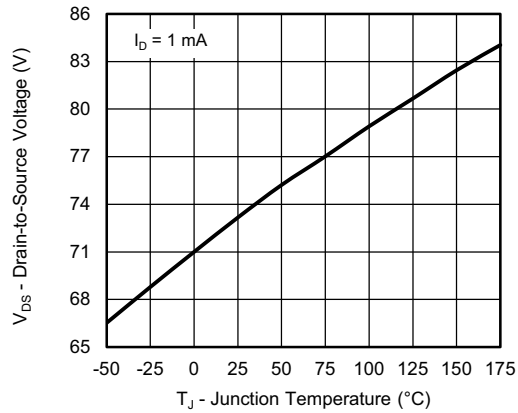
Threshold Voltage



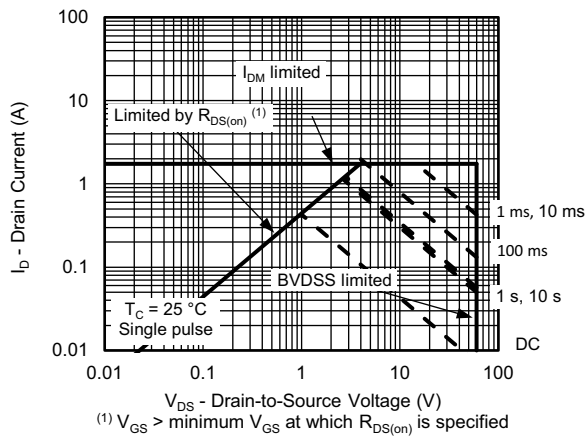
Threshold Voltage



TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

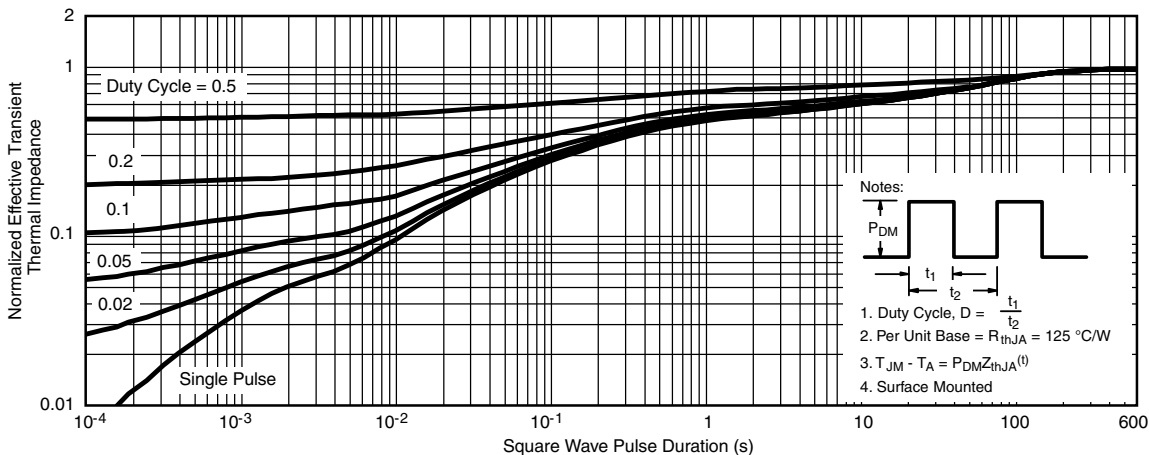


Drain Source Breakdown vs. Junction Temperature

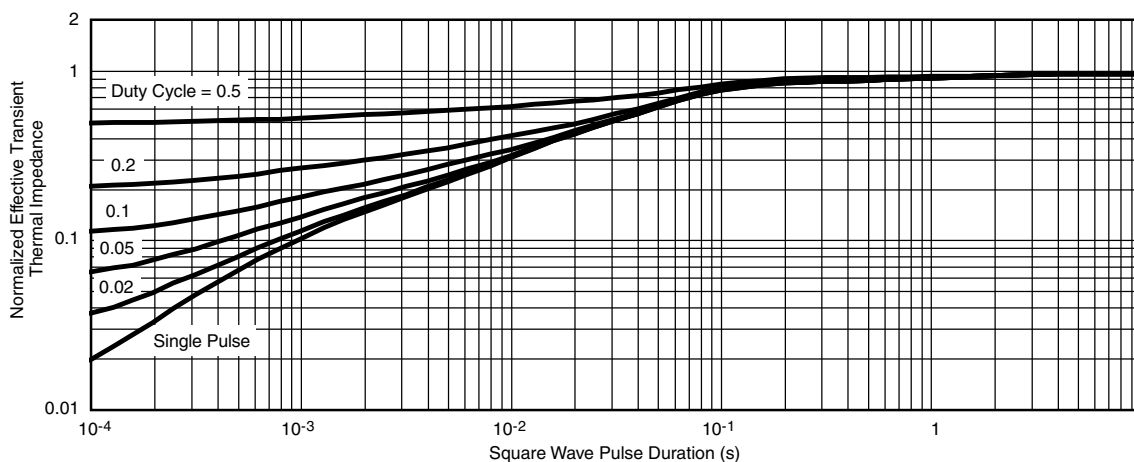




THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Foot ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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